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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Examiner: Dang, Phuc

Patent No.: 6,794,709 B2

Group Art Unit: 2818

Issue Date: September 21, 2004

Docket No: 303.678US3

Title: STRUCTURE AND METHOD FOR DUAL GATE OXIDE THICKNESSES

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450


**Certificate**  
**MAR 03 2005**  
**of Correction**

We are transmitting herewith the attached:

- ☒ A check in the amount of \$100.00 to cover the Certificate of Correction fee.
- ☒ Request for Certificate of Correction.
- ☒ Certificate of Correction Form - PTO-1050 (in duplicate)
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**Please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.**

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
Customer No: 21186

By:   
Name: David C. Peterson  
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Stephanie Bangston  
Name

Stephanie Bangston  
Signature

**MAR 04 2005**

Patent 6,794,709

PATENT

**IN UNITED STATES PATENT AND TRADEMARK OFFICE**

Patent No.: 6,794,709 *B2*

Docket No: 303.678US3

Issue Date: September 21, 2004

Patentee: Kie Y. Ahn et al.

Customer No.: 21186

Confirmation No.: 9583

*Title* STRUCTURE AND METHOD FOR DUAL GATE OXIDE THICKNESSES

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**REQUEST FOR CERTIFICATION OF CORRECTION**

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. Two copies of the text of the Certificate in the suggested form are enclosed.

**Pursuant to 1.20(a), enclosed please find a check in the amount of \$100.00.**

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

The Examiner is authorized to charge any additional fees or credit overpayment to Deposit Account No.19-0743.

Respectfully Submitted

KIE Y. AHN ET AL.

By their Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
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Date: 2-18-05

By: *[Signature]*

David C. Peterson  
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Stephanie Bangston  
Name

*[Signature]*  
Signature

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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 6,794,709 *B2*  
 DATED : September 21, 2004  
 INVENTOR(S) : Ahn et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 2, after "Park et al." insert - - 156 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 3, after "Okazawa" insert - - 357 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 4, after "Lowrey et al." insert - - 438 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 5, after "Liu et al." insert - - 257 - -.

On the face page, in field (56), under "U.S. Patent Documents", in column 1, line 7, after "Cavins et al." insert - - 438 - -.

On page 2, in field (56), under "U.S. Patent Documents", in column 1, line 2, after "Hasegawa" insert - - 257 - -.

On page 2, in field (56), under "Other Publications", in column 1, line 14, delete "TiO<sub>2</sub> Si<sub>3</sub>N<sub>4</sub>" and insert - - TiO<sub>2</sub> Si<sub>3</sub>N<sub>4</sub> - -, therefor.

On page 2, in field (56), under "Other Publications", in column 1, line 20, insert - - Hideo, O., et al., "Dual Gate Oxide Process Integration for High Performance Embedded Memory Products", Extended Abstract of the 1998 International Conference on Solid State Devices and Materials, pp. 108-109, (1998) - -.

On page 2, in field (56), under "Other Publications", in column 2, line 21, delete "DRAMs" and insert - - DRAMs - -, therefor.

MAILING ADDRESS OF SENDER:

SCHWEGMAN, LUNDBERG, WOESSNER, & KLUTH, P.A.  
 P.O. BOX 2938  
 Minneapolis, MN 55402

Atty Docket No: 303.678US3

PATENT NO. 6,794,709

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In column 5, line 40, delete "1999International" and insert - - 1999 International - -, therefor.

In column 8, line 14, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 8, line 15, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 8, line 30, delete "source drain" and insert - - source/drain - -, therefor.

In column 8, line 33, delete "source drain" and insert - - source/drain - -, therefor.

In column 10, line 28, in Claim 4, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 10, line 29, in Claim 4, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 10, line 32, in Claim 5, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 10, line 39, in Claim 7, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 10, line 45, in Claim 8, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 10, line 46, in Claim 8, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 10, line 60, in Claim 11, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 10, line 61, in Claim 11, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 10, line 64, in Claim 12, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 11, line 21, in Claim 18, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 11, line 22, in Claim 18, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 11, line 25, in Claim 19, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 11, line 34, in Claim 21, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 11, line 44, in Claim 23, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 11, line 49, in Claim 25, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 11, line 49, in Claim 25, after "nitride" delete "(Si3N4)" and insert - - (Si<sub>3</sub>N<sub>4</sub>) - -, therefor.

In column 12, line 6, in Claim 30, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 12, line 29, in Claim 35, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 12, line 35, in Claim 36, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 12, line 50, in Claim 39, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

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In column 10, line 46, in Claim 8, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

In column 10, line 60, in Claim 11, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 10, line 61, in Claim 11, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

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In column 12, line 29, in Claim 35, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

In column 12, line 35, in Claim 36, delete "Si3N4" and insert - - Si<sub>3</sub>N<sub>4</sub> - -, therefor.

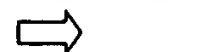
In column 12, line 50, in Claim 39, delete "SiO2" and insert - - SiO<sub>2</sub> - -, therefor.

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